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40V PNP SILICON PLANAR MEDIUM POWER TRANSISTOR IN SOT89

Features

- BV_{CEO} > -40V
- Maximum Continuous Current I_C = -1A
- Low saturation voltage V_{CE(sat)} < -500mV @ -1A
- Complementary NPN type: FCX491A
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT89
- Case material: molded plastic. "Green" molding compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 63
- Weight: 0.05 grams (Approximate)

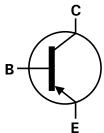
Application

- Power MOSFET & IGBT gate driving
- · Low loss power switching

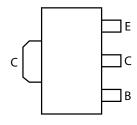
SOT89



Top View



Device Symbol



Top View Pin Out

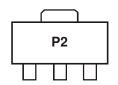
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FCX591ATA	P2	7	12	1,000
FCX591A-13R	P2	13	12	4,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



P2 = Product Type Marking Code





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	lc	-1	Α
Peak Pulse Current	Ісм	-2	Α
Peak Base Current	I _B	-200	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_{D}	1	W
Thermal Resistance, Junction to Ambient Air (Note 5)	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction to Leads (Note 6)	$R_{\theta JL}$	10.01	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	≥ 8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

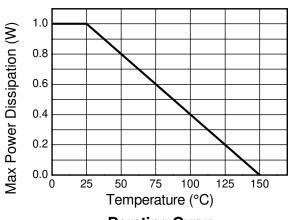
Notes:

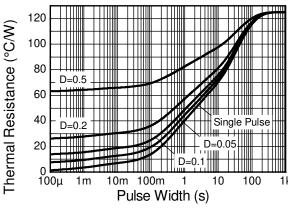
^{5.} For a device surface mounted on 15mm X 15mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; device measured when operating in steady state condition.

Thermal resistance from junction to solder-point (on the exposed collector pad).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



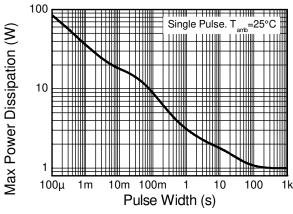
Thermal Characteristics and Derating Information





Derating Curve

Transient Thermal Impedance



Pulse Power Dissipation





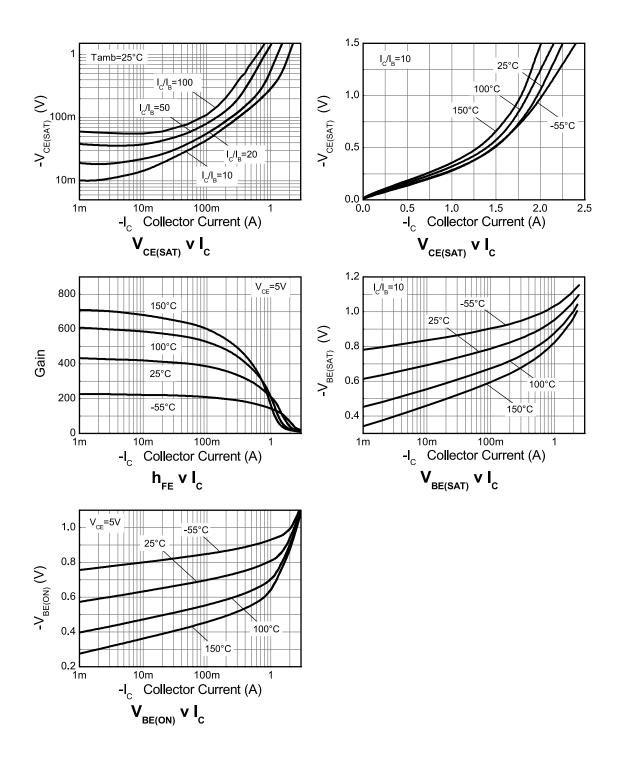
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-40	-	-	V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	-40	-	-	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-	-	V	$I_E = -100\mu A$
Collector Cutoff Current	I _{CBO}	-	-	-100	nA	$V_{CB} = -30V$
Emitter Cutoff Current	I _{EBO}	-	-	-100	nA	$V_{EB} = -4V$
Emitter Cutoff Current	I _{CES}	-	-	-100	nA	$V_{CES} = -30V$
DC current transfer Static ratio (Note 8)	h _{FE}	300 300 250 160 30	- - - -	- 800 - - -	-	$I_{C} = -1 \text{ mA}, V_{CE} = -5 \text{ V}$ $I_{C} = -100 \text{ mA}, V_{CE} = -5 \text{ V}$ $I_{C} = -500 \text{ mA}, V_{CE} = -5 \text{ V}$ $I_{C} = -1 \text{ A}, V_{CE} = -5 \text{ V}$ $I_{C} = -2 \text{ A}, V_{CE} = -5 \text{ V}$
Collector-Emitter Saturation Voltage (Note 8)	$V_{CE(sat)}$	-	-	-0.2 -0.35 -0.5	V	$I_C = -100$ mA, $I_B = -1$ mA $I_C = -500$ mA, $I_B = -20$ mA $I_C = -1$ A, $I_B = -100$ mA
Base-Emitter Saturation Voltage (Note 8)	$V_{BE(sat)}$	-	-	-1.1	V	$I_C = -1A$, $I_B = -50mA$
Base-Emitter Turn-on Voltage (Note 8)	$V_{BE(on)}$	-	-	-1.0	V	$I_C = -1A$, $V_{CE} = -5V$
Transitional Frequency	f⊤	150	-	-	MHz	$I_E = -50 \text{mA}, V_{CE} = -10 \text{V}$ f = 100MHz
Output capacitance	C_{obo}	-	-	10	pF	$V_{CB} = -10V$, $f = 1MHz$,

Notes: 8. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



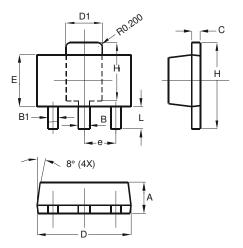
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

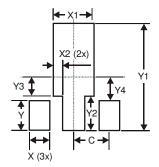
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT89				
Dim	Min	Max		
Α	1.40	1.60		
В	0.44	0.62		
B1	0.35	0.54		
С	0.35	0.44		
D	4.40	4.60		
D1	1.62	1.83		
Е	2.29	2.60		
е	1.50 Typ			
Η	3.94	4.25		
H1	2.63	2.93		
L	0.89	1.20		
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Х	0.900
X1	1.733
X2	0.416
Υ	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
С	1.500





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